

PS7841-A11, PS7841-A15**FOR OPTICAL DAA
16-PIN SSOP OCMOS FET****DESCRIPTION**

The PS7841-A11 and PS7841-A15 are solid state relays for optical DAA (Data Access Arrangement). They have an OCMOS FET, photocoupler, diode bridge and darlington transistor.

This device is suitable for analog signal control applications such as laptop PCs, modem cards, voice telephony and fax machines.

★ FEATURES

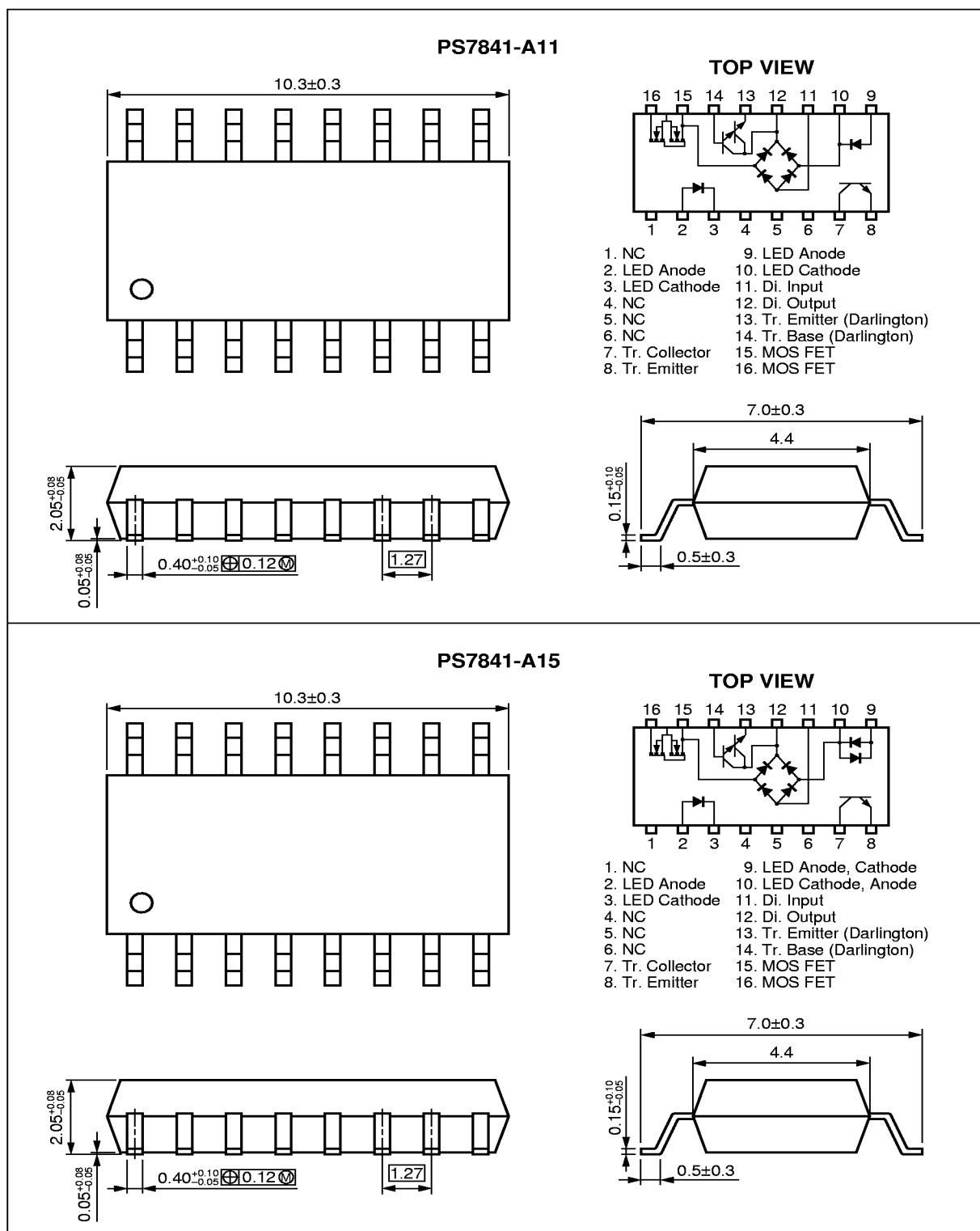
- For optical DAA circuit
 - OCMOS FET
 - Photocoupler DC input response : PS7841-A11
 AC input response : PS7841-A15
 - Diode bridge
 - Darlington transistor
- Low LED Operating Current ($I_F = 2 \text{ mA}$)
- Small and thin package (16-pin SSOP: 255 mil, Pin pitch = 1.27 mm, Height = 2.1 mm)
- Ordering number of taping product: PS7841-A11-F3, F4, PS7841-A15-F3, F4
- UL approved: File No. E72422 (S)

APPLICATIONS

- Laptop PC, PDA
- Modem card
- Telephone, FAX

The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version.
Not all devices/types available in every country. Please check with local NEC representative for availability and additional information.

★ PACKAGE DIMENSIONS (in millimeters)



ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise specified)

Parameter			Symbol	Ratings	Unit
OCMOS FET (Pin No. 2, 3, 15, 16)	Diode	Forward Current (DC)	I _F	50	mA
		Reverse Voltage	V _R	5.0	V
		Power Dissipation	P _D	50	mW
		Peak Forward Current ^{*1}	I _{FP}	1	A
	MOS FET	Break Down Voltage	V _L	400	V
		Continuous Load Current	I _L	120	mA
		Pulse Load Current ^{*2} (AC/DC Connection)	I _{LP}	250	mA
		Power Dissipation	P _D	430	mW
Photocoupler (Pin No. 7, 8, 9, 10)	Diode	Forward Current	I _F	50	mA
		Reverse Voltage ^{*3}	V _R	5.0	V
		Power Dissipation	P _D	50	mW
		Peak Forward Current ^{*1}	I _{FP}	1	A
	Transistor	Collector to Emitter Voltage	V _{CEO}	40	V
		Collector Current	I _C	80	mA
		Power Dissipation	P _C	50	mW
Diode Bridge (Pin No. 10, 11, 12, 15)	Forward Current		I _F	140	mA
	Reverse Voltage		V _R	100	V
Darlington Transistor (Pin No. 12, 13, 14)	Collector to Emitter Voltage		V _{CEO}	40	V
	Collector Current		I _C	120	mA
	Power Dissipation		P _C	500	mW
Isolation Voltage ^{*4}			BV	1 500	Vr.m.s.
Total Power Dissipation			P _T	650	mW
Operating Ambient Temperature			T _A	−40 to +80	°C
Storage Temperature			T _{stg}	−40 to +100	°C

*1 PW = 100 μs, Duty Cycle = 1 %

*2 PW = 100 ms, 1 shot

*3 PS7841-A11 only

*4 AC voltage for 1 minute at T_A = 25 °C, RH = 60 % between input and output

RECOMMENDED OPERATING CONDITIONS (T_A = 25 °C)

Parameter		Symbol	MIN.	TYP.	MAX.	Unit
OCMOS FET	LED Operating Current	I _F	2	10	20	mA
	LED Off Voltage	V _F	0		0.5	V

ELECTRICAL CHARACTERISTICS (T_A = 25 °C)

★ OCMOS FET (Pin No. 2, 3, 15, 16)

Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Diode	Forward Voltage	V _F	I _F = 10 mA		1.2	1.4	V
MOS FET	Off-state Leakage Current	I _{loff}	V _D = 400 V			1.0	μA
Coupled	LED On-state Current	I _{Fon}	I _L = 120 mA			2.0	mA
	On-state Resistance	R _{on1}	I _F = 10 mA, I _L = 10 mA		20	30	Ω
		R _{on2}	I _F = 10 mA, I _L = 120 mA		16	25	
	Turn-on Time	t _{on}	I _F = 10 mA, V _O = 5 V, PW ≥ 10 ms		0.3	1.0	ms
	Turn-off Time	t _{off}			0.04	0.2	
	Isolation Resistance	R _{I-O}	V _{I-O} = 500 V _{DC}	10 ⁹			Ω
	Isolation Capacitance	C _{I-O}	V = 0 V, f = 1 MHz		1.1		pF

PHOTOCOUPLER (Pin No. 7, 8, 9, 10)

Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Diode	Forward Voltage	V _F	I _F = 10 mA		1.2	1.4	V
Transistor	Collector to Emitter Dark Current	I _{CEO}	V _{CE} = 40 V, I _F = 0 mA			0.1	μA
Coupler	Current Transfer Ratio (I _C /I _F)	CTR	I _F = 5 mA, V _{CE} = 5 V	50	200	400	%
	Collector Saturation Voltage	V _{CE(sat)}	I _F = 10 mA, I _C = 2 mA		0.1	0.3	V
	Rise Time	t _r	V _{CC} = 5 V, I _C = 2 mA, R _L = 100 Ω		3.0		μs
	Fall Time	t _f			5.0		
	Isolation Resistance	R _{I-O}	V _{I-O} = 500 V _{DC}	10 ¹¹			Ω
	Isolation Capacitance	C _{I-O}	V = 0 V, f = 1 MHz		0.4		pF

DIODE BRIDGE (Pin No. 10, 11, 12, 15)

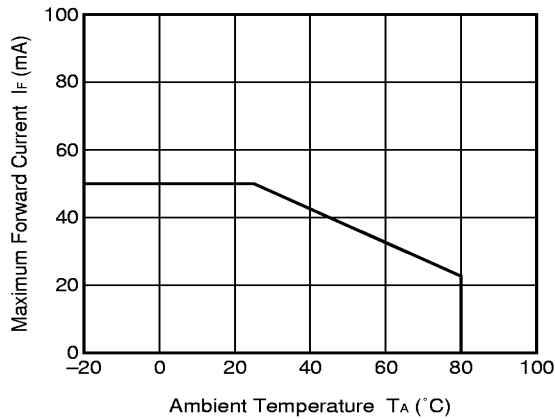
Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Forward Voltage		V _F	I _F = 120 mA		0.9	1.2	V
Reverse Current		I _R	V _R = 100 V			10	μA

DARLINGTON TRANSISTOR (Pin No. 12, 13, 14)

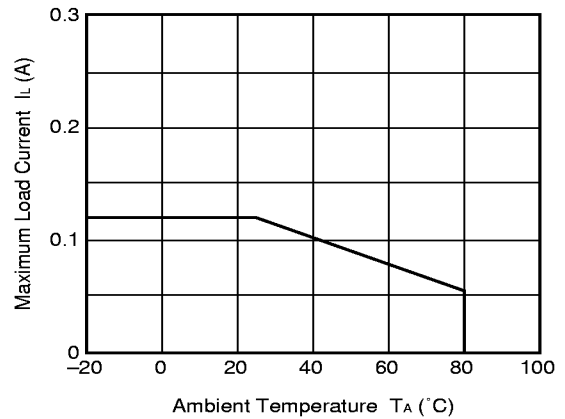
Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
★	Collector Saturation Voltage	V _{CE(sat)}	I _C = 120 mA, I _B = 100 μA		1.0	1.4	V
	Collector to Emitter Dark Current	I _{CEx}	I _B = 0 mA, V _{CE} = 30 V		0.01	1.0	μA
★	DC Current Gain	h _{FE}	I _C = 120 mA, V _{CE} = 10 V	10 000	35 000		

★ OCMOS TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)

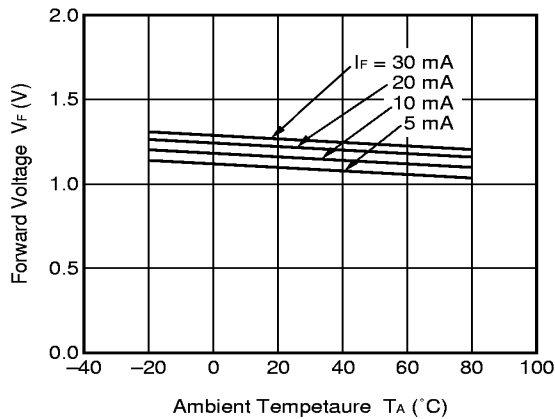
MAXIMUM FORWARD CURRENT vs. AMBIENT TEMPERATURE



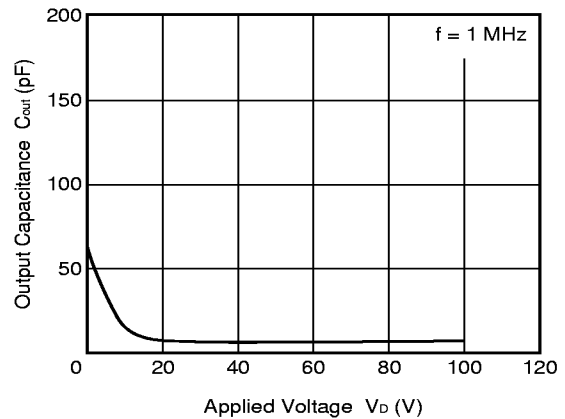
MAXIMUM LOAD CURRENT vs. AMBIENT TEMPERATURE



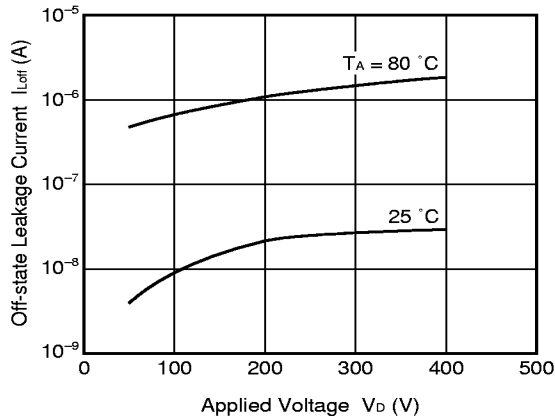
FORWARD VOLTAGE vs. AMBIENT TEMPERATURE



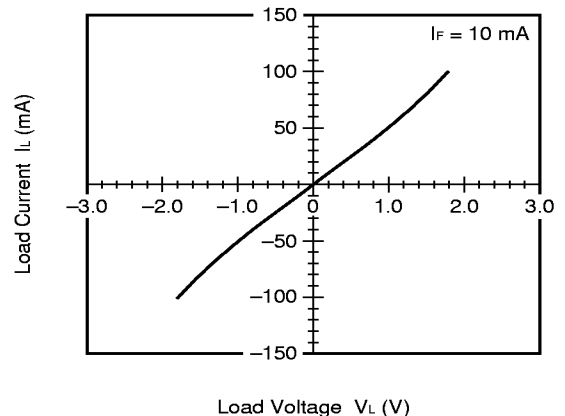
OUTPUT CAPACITANCE vs. APPLIED VOLTAGE



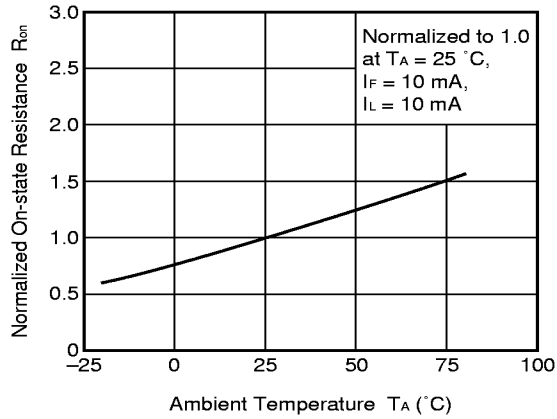
OFF-STATE LEAKAGE CURRENT vs. APPLIED VOLTAGE



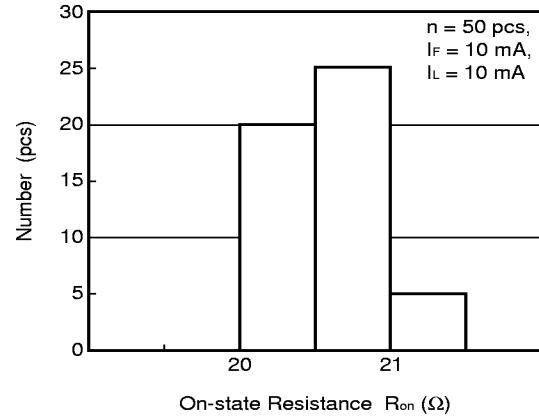
LOAD CURRENT vs. LOAD VOLTAGE



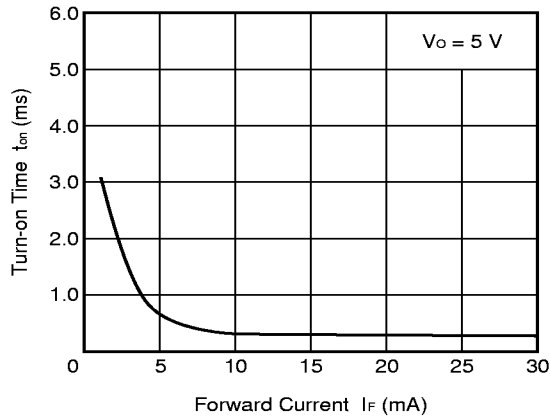
NORMALIZED ON-STATE RESISTANCE vs. AMBIENT TEMPERATURE



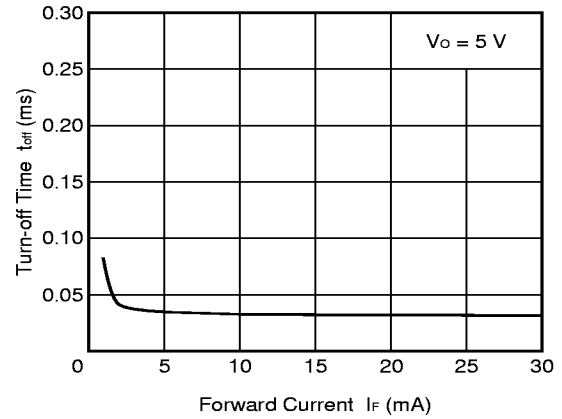
ON-STATE RESISTANCE DISTRIBUTION



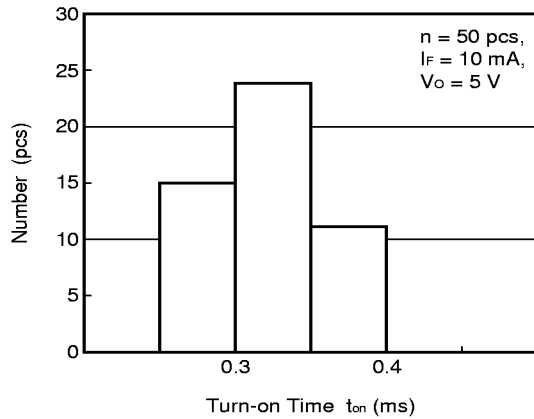
TURN-ON TIME vs. FORWARD CURRENT



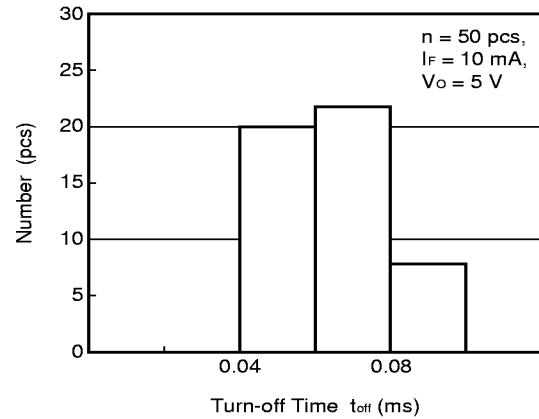
TURN-OFF TIME vs. FORWARD CURRENT



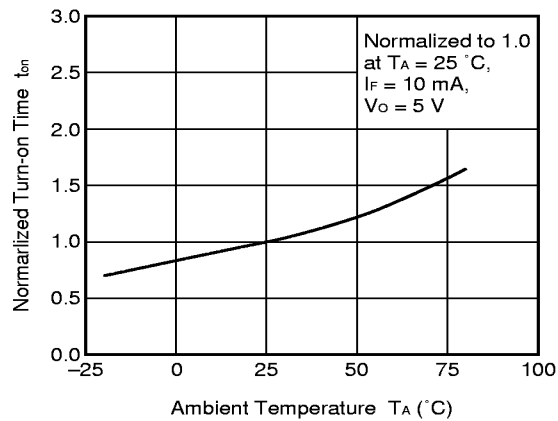
TURN-ON TIME DISTRIBUTION



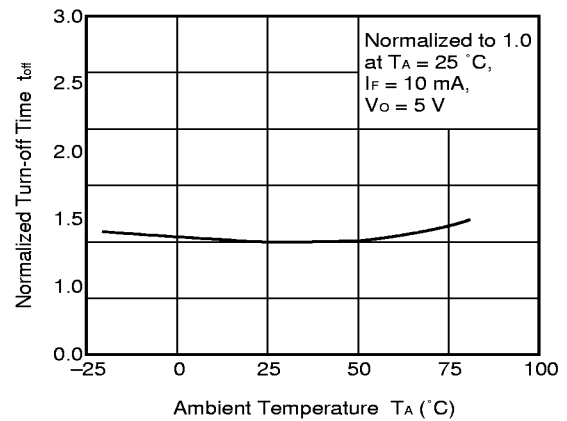
TURN-OFF TIME DISTRIBUTION



NORMALIZED TURN-ON TIME vs.
AMBIENT TEMPERATURE



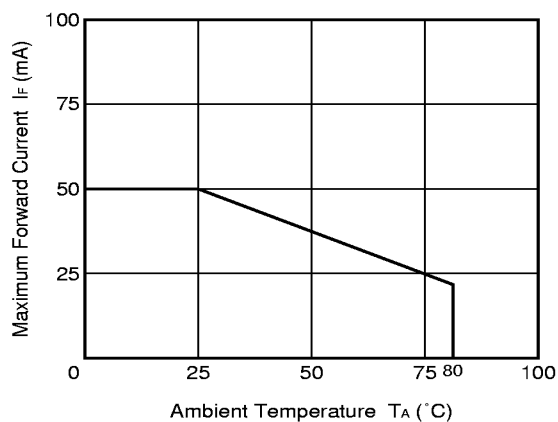
NORMALIZED TURN-OFF TIME vs.
AMBIENT TEMPERATURE



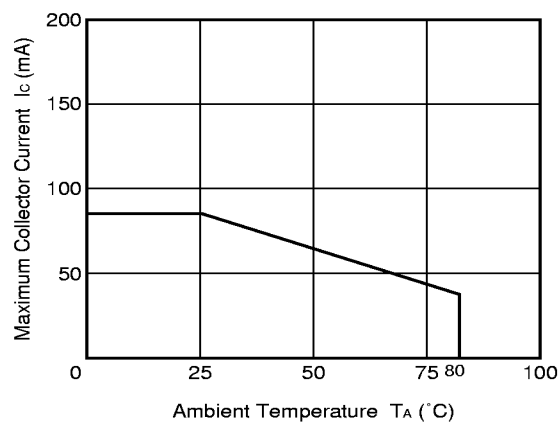
Remark The graphs indicate nominal characteristics.

★ PHOTOCOUPLER TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, unless otherwise specified)

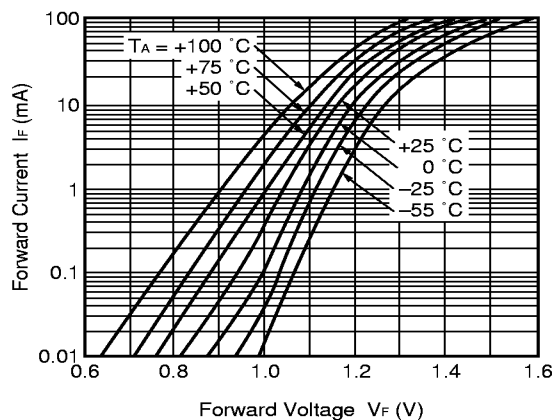
MAXIMUM FORWARD CURRENT vs. AMBIENT TEMPERATURE



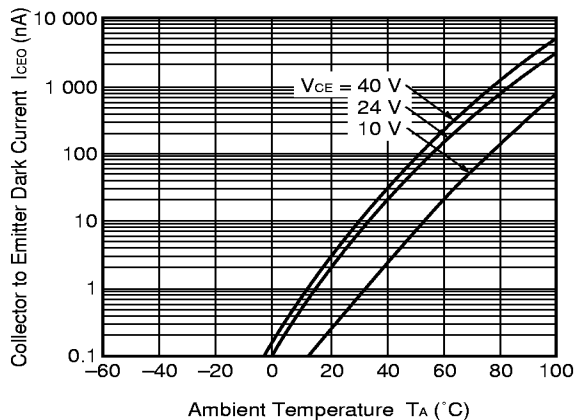
MUXIMUM COLLECTOR CURRENT vs. AMBIENT TEMPERATURE



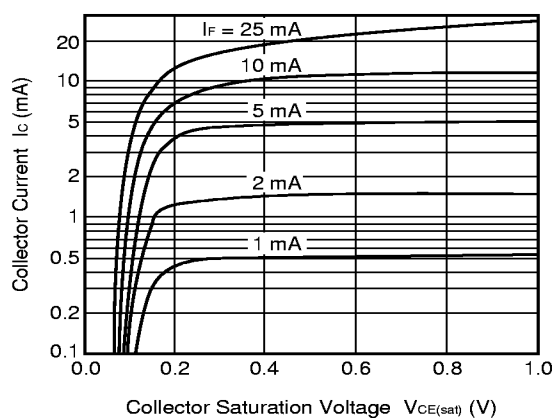
FORWARD CURRENT vs. FORWARD VOLTAGE



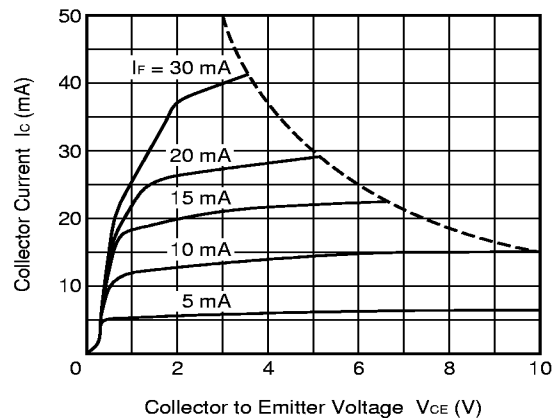
COLLECTOR TO EMITTER DARK CURRENT vs. AMBIENT TEMPERATURE



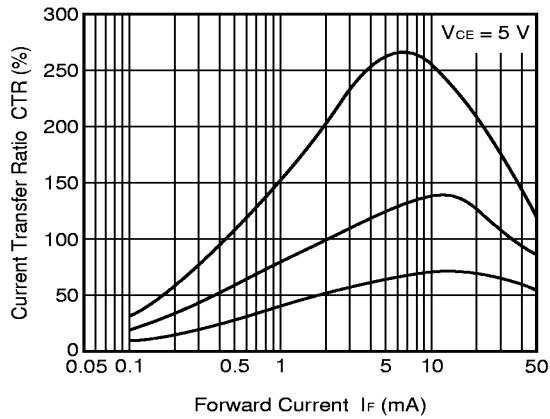
COLLECTOR CURRENT vs. COLLECTOR SATURATION VOLTAGE



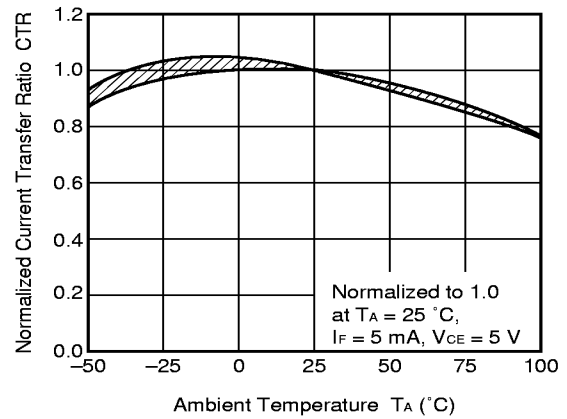
COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE



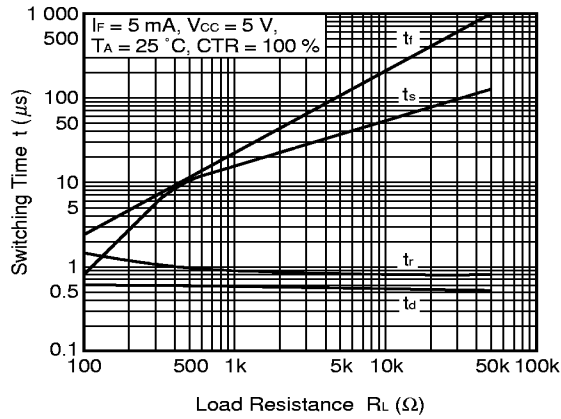
CURRENT TRANSFER RATIO vs.
FORWARD CURRENT



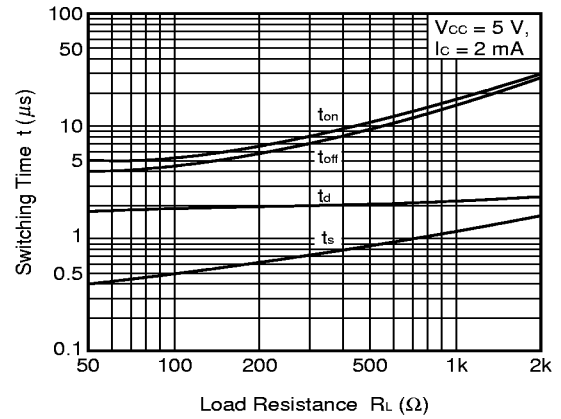
NORMALIZED CURRENT TRANSFER
RATIO vs. AMBIENT TEMPERATURE



SWITCHING TIME vs.
LOAD RESISTANCE



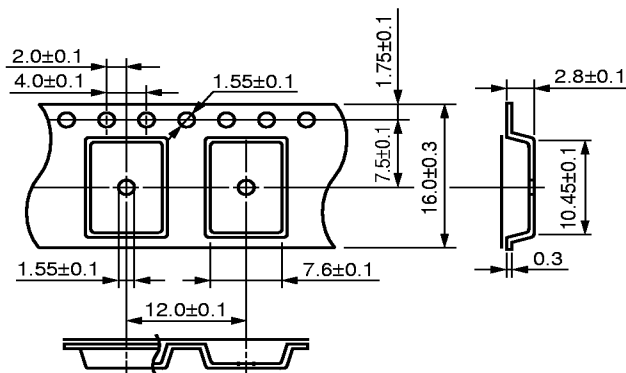
SWITCHING TIME vs.
LOAD RESISTANCE



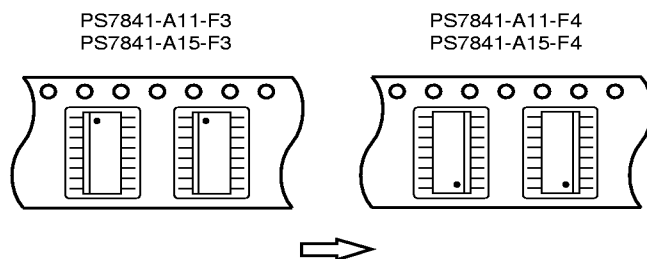
Remark The graphs indicate nominal characteristics.

★ TAPING SPECIFICATIONS (in millimeters)

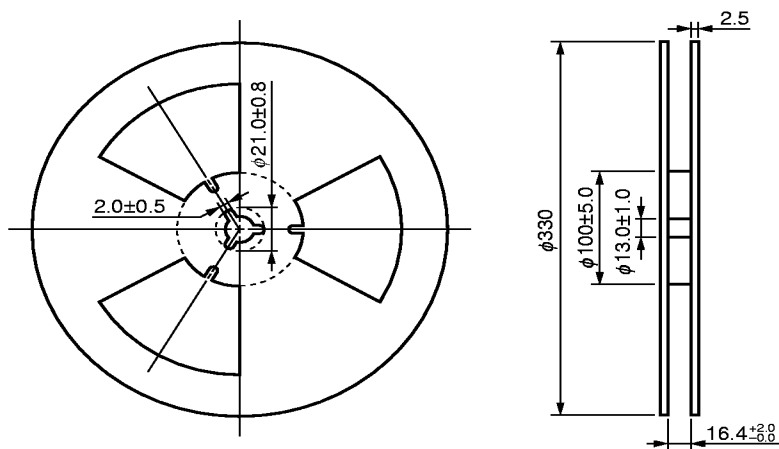
Outline and Dimensions (Tape)



Tape Direction



Outline and Dimensions (Reel)



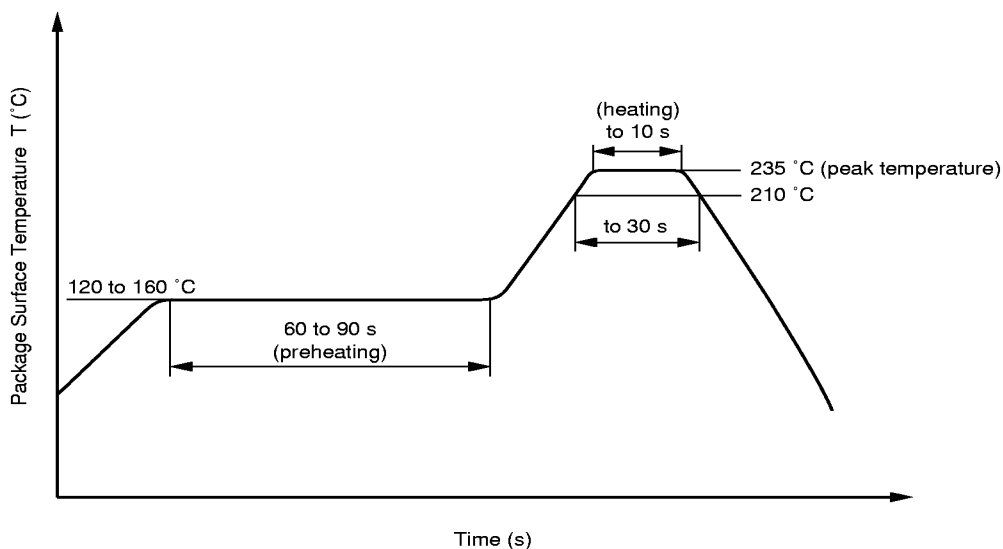
Packing: 1 500pcs/reel

★ **RECOMMENDED SOLDERING CONDITIONS**

(1) Infrared reflow soldering

- Peak reflow temperature 235 °C (package surface temperature)
- Time of temperature higher than 210 °C 30 seconds or less
- Number of reflows One
- Flux Rosin flux containing small amount of chlorine (The flux with a maximum chlorine content of 0.2 Wt % is recommended.)

Recommended Temperature Profile of Infrared Reflow



(2) Dip soldering

- Temperature 260 °C or below (molten solder temperature)
- Time 10 seconds or less
- Number of times One
- Flux Rosin flux containing small amount of chlorine (The flux with a maximum chlorine content of 0.2 Wt % is recommended.)

(3) Cautions

- Fluxes
 - Avoid removing the residual flux with freon-based and chlorine-based cleaning solvent.